

isc P-Channel MOSFET Transistor

IRF9530NS

·FEATURES

- Static drain-source on-resistance: R_{DS}(on)≤200mΩ(@V_{GS}= -10V; I_D= -8.4A)
- Advanced trench process technology
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

• Fast switching application.



pin 1, Gate 2, Drain 3, Source TO-263 Package

	В			s
С	D —	K	Q	
J	ы <u>Н</u> ,	4	R	90

	mm		
DIM	MIN	MAX	
Α	1	0	
В	6.6	6.8	
C	15.23	15.25	
D	10.15	10.17	
F	0.76	0.78	
G	1.26	1.28	
Н	1.4	1.6	
J	1.33	1.35	
K	0.4	0.6	
L	4.6	4.8	
0	8.69	8.71	
R	5.28	5.30	
S	1.26	1.28	
U	0.0	0.2	
٧	0.37	0.39	
W	2.80	2.82	

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	-100	V
V _G s	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	-14	А
P _D	Total Dissipation @T _C =25°C	79	W
Tj	Max. Operating Junction Temperature	-55~175	°C
T _{stg}	Storage Temperature	-55~175	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	1.9	°C/W



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = -250 μ A	-100		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D = -250 μ A	-2	-4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = -10V; I _D = -8.4A		200	mΩ
Igss	Gate-Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0V		±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = -100V; V _{GS} = 0V		-25	μА
V _{SD}	Diode forward voltage	I _S = -8.4A, V _{GS} = 0V		-1.6	V



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